

# N-Channel 20V (D-S) Power MOSFET

### **Features**

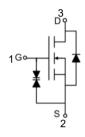
- 100% Avalanche Tested
- Halogen Free, Pb-Free
- RoHS Compliant



SOT-23

### **Applications**

- Relay driver
- Switching circuits
- High-side load switch
- High-speed line driver



Absolute Maximum Ratings (T <sub>A</sub> =25°C unless otherwise noted)					
Parameter	Symbol	Value	Unit		
Drain Source Voltage	V <sub>DS</sub>	20	V		
Gate Source Voltage	V <sub>G</sub> s	±8	V		
Drain Current, Continuous V <sub>GS</sub> =10V( <i>Note 1</i> )			6.5	Α	
Drain Current, Pulsed (Note 2)	I <sub>DM</sub>	30	А		
Power Dissipation( <i>Note 3</i> ) T <sub>C</sub> =25°C		P <sub>D</sub>	1.4	W	
Operating Junction/ Storage Tempera	TJ/ TSTG	-55 to +150	°C		

Note 1: Calculated continuous current based on maximum allowable junction temperature.

Note 3: The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.

Thermal Characteristics					
Parameter	Symbol	Max	Unit		
Thermal Resistance Junction to Ambient (Note 4)	R <sub>thJA</sub>	90	°C/W		

Note 4: The value of R<sub>BJA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with TA =25  $^{\circ}$ C

Note 2: Repetitive rating; pulse width limited by max. junction temperature.



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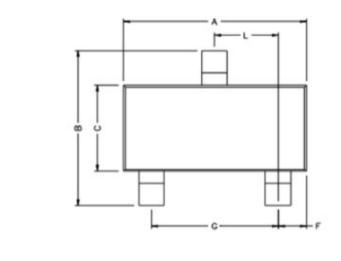
Electrical Characteristics (T <sub>A</sub> =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Drain Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	uA
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250uA	0.4		1	V
Octobordon Ormant		V <sub>GS</sub> =±4.5V, V <sub>DS</sub> =0V			±1	uA
Gate Leakage Current	Igss	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	uA
Drain-Source On-state	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6.5A		18	22	mΩ
Resistance		V <sub>GS</sub> =2.5V, I <sub>D</sub> =5.5A		24	30	
Total Gate Charge	Qg	V <sub>GS(off)</sub> =0V, V <sub>GS(on)</sub> =4.5V, V <sub>DD</sub> =10V, I <sub>D</sub> =6.5A		10		
Gate-Source Charge	Q <sub>gs</sub>			2.3		nC
Gate-Drain Charge	$Q_{gd}$	. 101, 15 0.0.1		3		
Turn-on Delay Time	t <sub>d(on)</sub>			6.5		
Turn-on Rise Time	t <sub>r</sub>	V <sub>GS</sub> =5V, V <sub>DD</sub> =10V,		13		
Turn-off Delay Time	t <sub>d(off)</sub>	$I_D=1A$ , $R_G=3\Omega$		50		ns
Turn-off Fall Time	t <sub>f</sub>			30		
Input Capacitance	C <sub>iss</sub>			1160		
Output Capacitance	Coss	V <sub>GS=</sub> 0V, V <sub>DS</sub> =10V, f=1MHz		200		pF
Reverse Transfer Capacitance	Crss			140		

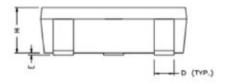
Reverse Diode Characteristics (T <sub>A</sub> =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Continuous Source Current (Body Diode)	Is	Tc=25°C			6.5	Α
Pulsed Source Current (Body Diode)	I <sub>SM</sub>	T <sub>C</sub> =25°C			30	Α
Diode Forward Voltage	V <sub>SD</sub>	I <sub>s</sub> =1A, V <sub>GS</sub> =0V		0.76	1	V

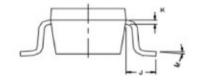


## Package Outline Dimensions (Unit: millimeters)

## **SOT-23**





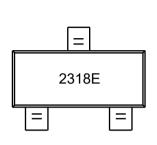


DEE Milli		meter	DEE	Millimete		
REF.	Min.	Max.	REF.	Min.	Max.	
Α	2.80	3.00	G	1.80	2.00	
В	2.30	2.50	Н	0.90	1.1	
С	1.20	1.40	K	0.10	0.20	
D	0.30	0.50	J	0.35	0.70	
E	0	0.10	L	0.92	0.98	
F	0.45	0.55	M	0°	10°	



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## **Marking Outline**



Part Name: SSF2318E

1. P/N Mark: 2318E

## **Revision History**

Version	Date	Major Changes
Rev.A	2025.07.03	Official Release



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